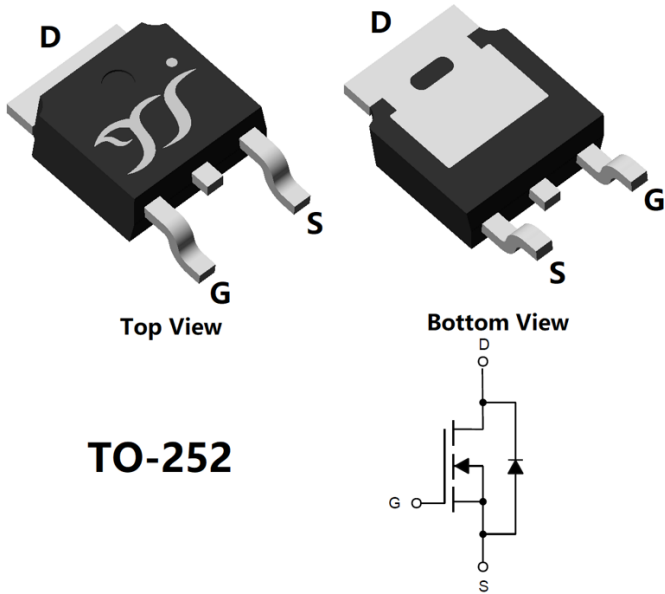


N-Channel Enhancement Mode Field Effect Transistor



TO-252

Product Summary

- V_{DS} 100V
- I_D 15A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) <110mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) <120mohm
- 100% EAS Tested
- 100% ∇V_{DS} Tested

General Description

- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- DC-DC Converters
- Power management functions

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	100	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	$T_C=25^\circ C$	15
		$T_C=100^\circ C$	9.5
Pulsed Drain Current ^A	I_{DM}	60	A
Single Pulse Avalanche Energy ^B	E_{AS}	9	mJ
Total Power Dissipation	P_D	$T_C=25^\circ C$	28
		$T_C=100^\circ C$	11
Thermal Resistance Junction-to-Case ^C	$R_{\theta JC}$	4.4	$^\circ C/W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJD15N10A	F1/F2	YJD15N10A	2500	/	25000	13" reel



YJD15N10A

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	T _J =25°C		1	μA
			T _J =150°C		100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.1	1.8	2.5	V
Static Drain-Source On-Resistance	R _{D(S(ON))}	V _{GS} =10V, I _D =8A		95	110	mΩ
		V _{GS} =4.5V, I _D =8A		100	120	
Diode Forward Voltage	V _{SD}	I _S =15A, V _{GS} =0V		0.8	1.2	V
Maximum Body-Diode Continuous Current	I _S				15	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHZ		1070		pF
Output Capacitance	C _{oss}			33		
Reverse Transfer Capacitance	C _{rss}			30		
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =50V, I _D =10A		26		nC
Gate-Source Charge	Q _{gs}			5.4		
Gate-Drain Charge	Q _{gd}			5.8		
Reverse Recovery Charge	Q _{rr}	I _F =10A, di/dt=100A/us		30.1		ns
Reverse Recovery Time	t _{rr}			40		
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =50V, R _L =6.4Ω R _{GEN} =3Ω		7		ns
Turn-on Rise Time	t _r			24		
Turn-off Delay Time	t _{D(off)}			24		
Turn-off fall Time	t _f			31		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. T_J=25°C, V_{DD}=50V, V_G=10V, L=0.5mH, I_{AS}=6A

C. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{θJC} is guaranteed by design, while R_{θJA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper



■ Typical Performance Characteristics

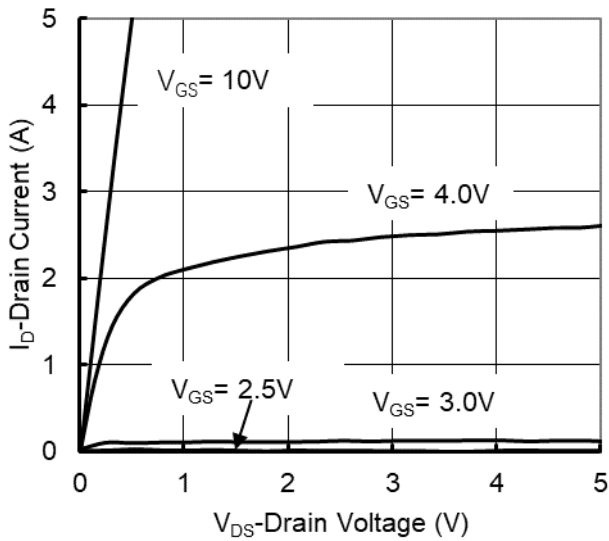


Figure 1. Output Characteristics

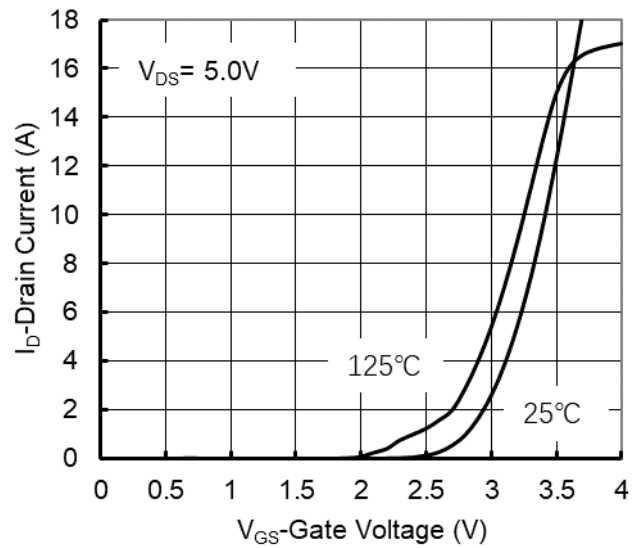


Figure 2. Transfer Characteristics

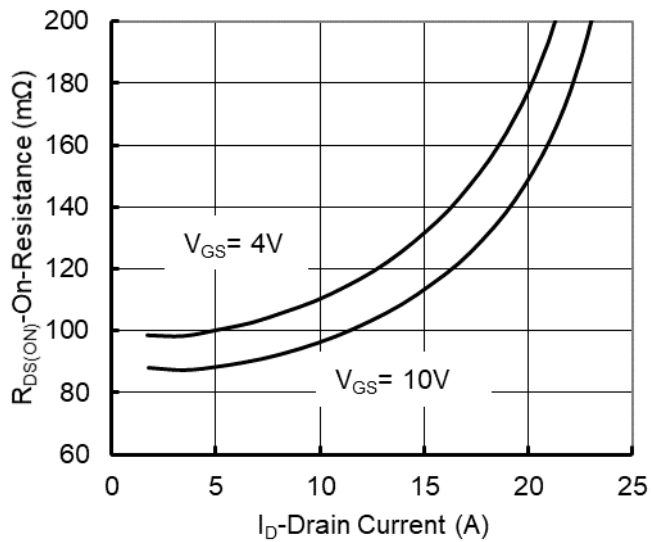


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

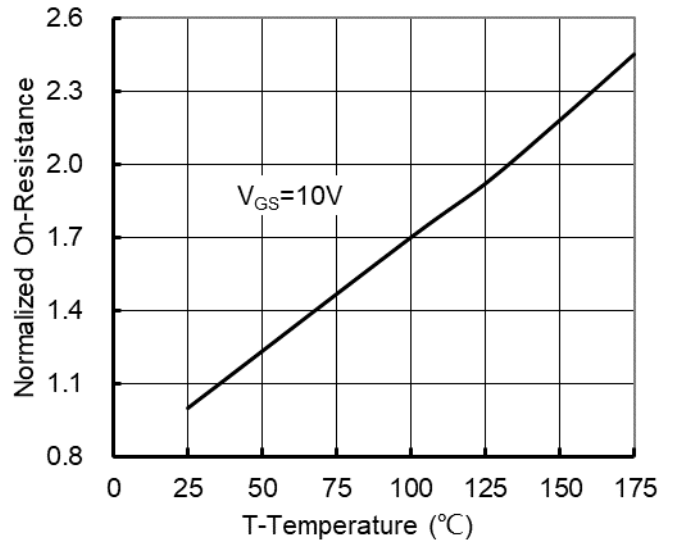


Figure 4. On-Resistance vs. Junction Temperature

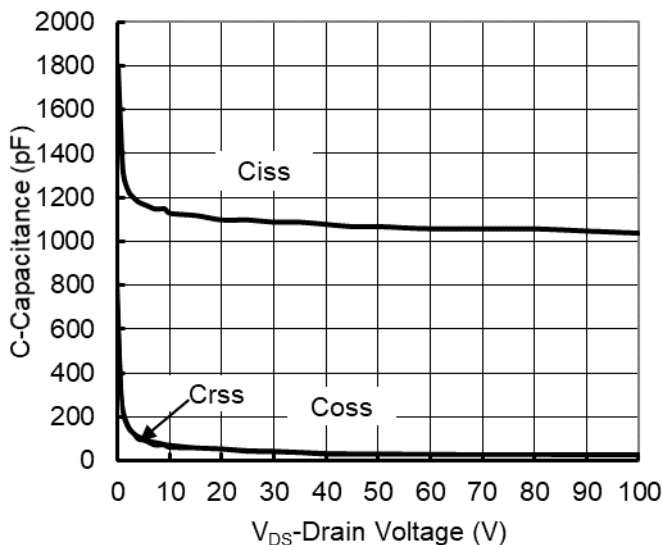


Figure 5. Capacitance Characteristics

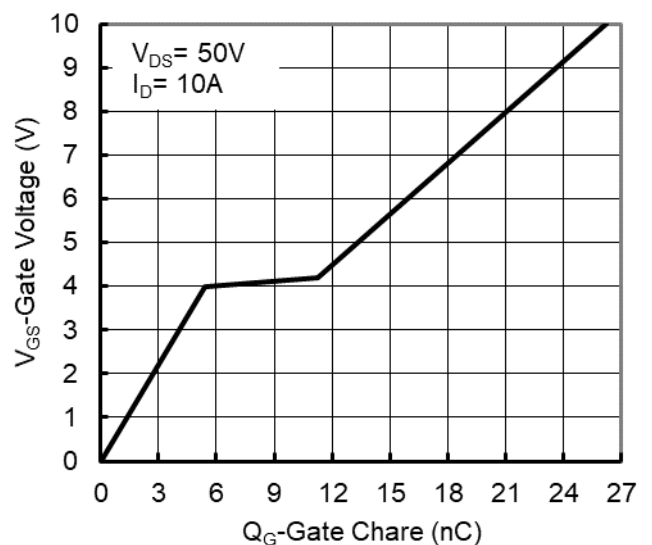


Figure 6. Gate Charge



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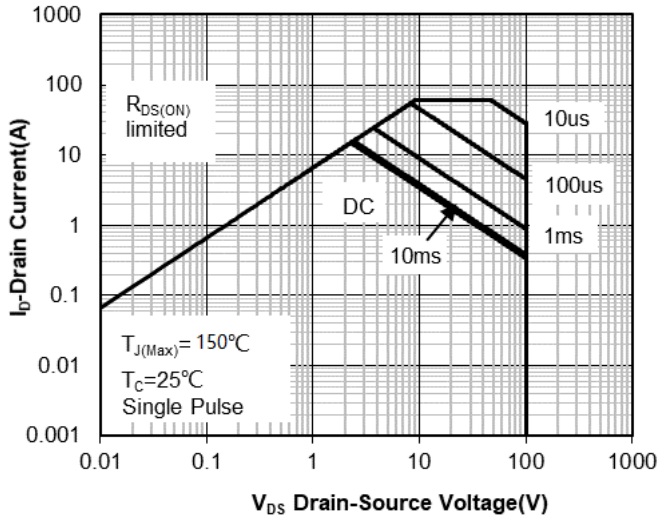


Figure 7. Safe Operation Area

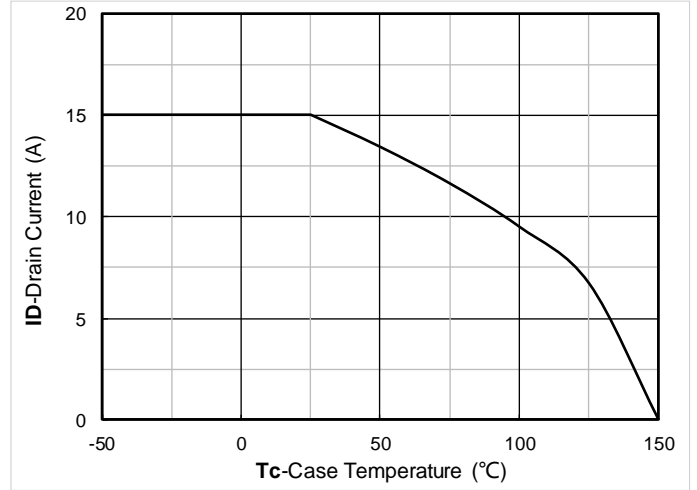


Figure 8. Maximum Continuous Drain Current vs Case Temperature

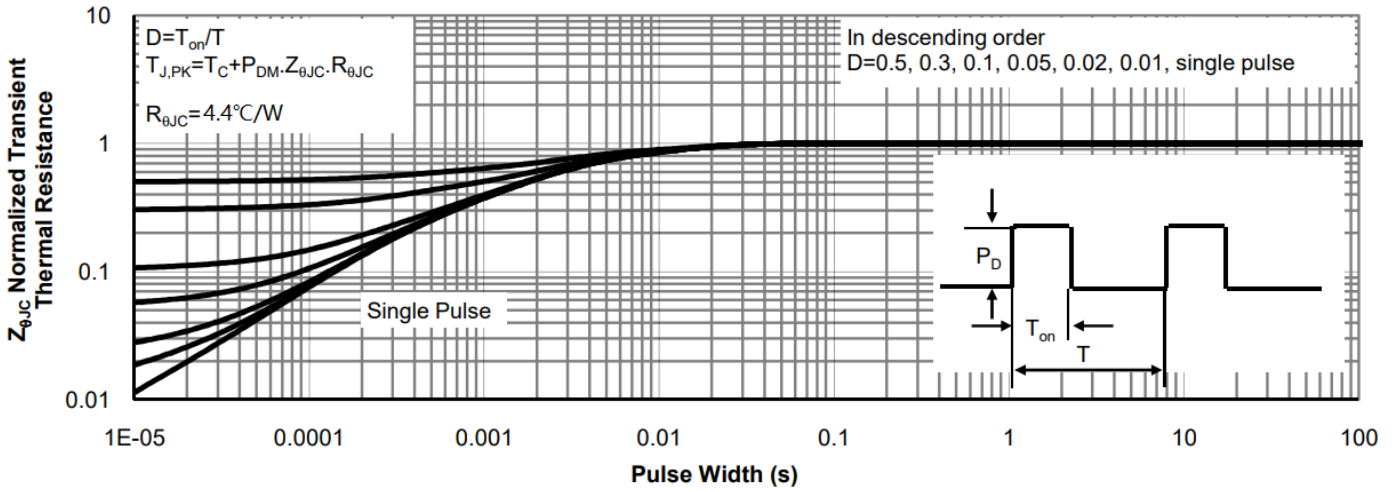
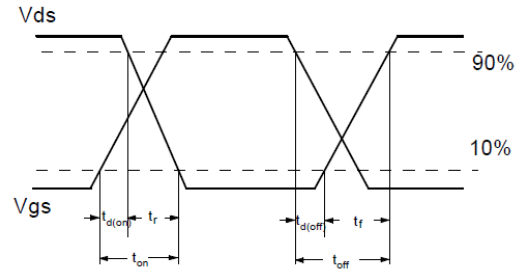
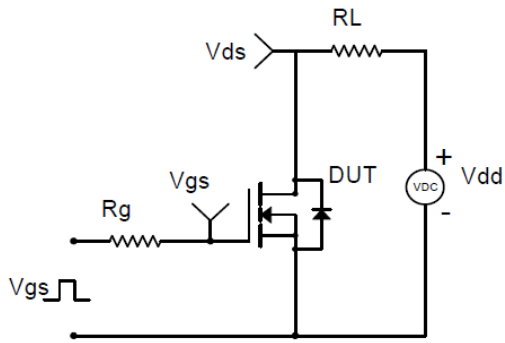
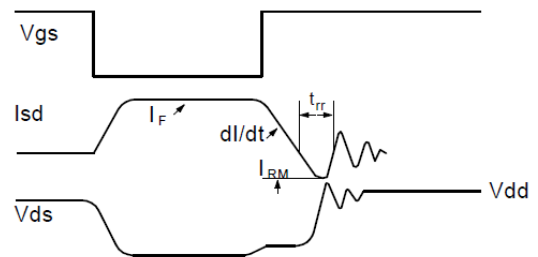
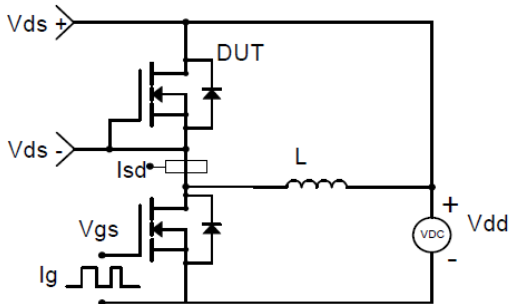


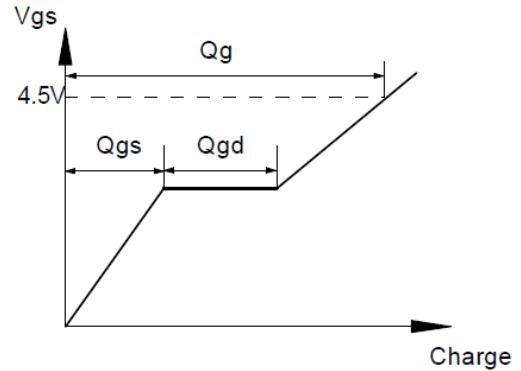
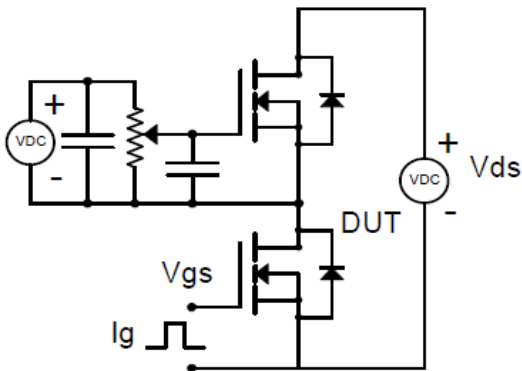
Figure 9. Normalized Maximum Transient Thermal Impedance



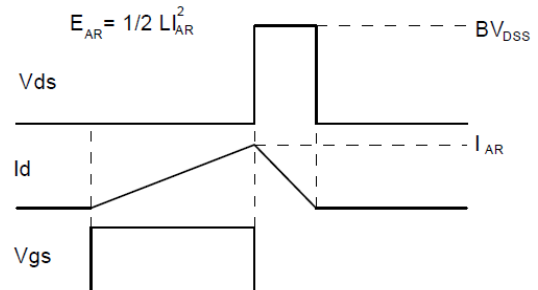
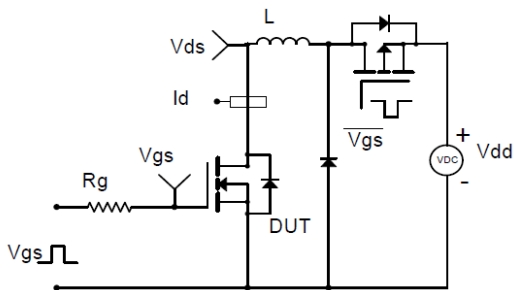
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Gate Charge Test Circuit & Waveform

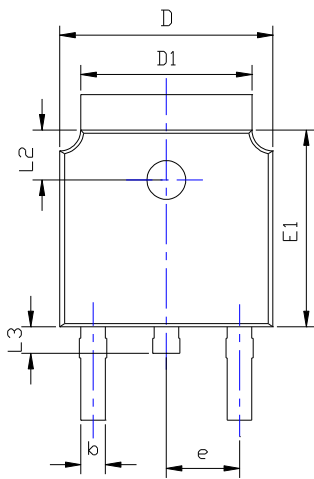


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

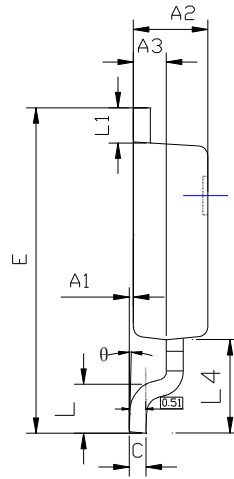


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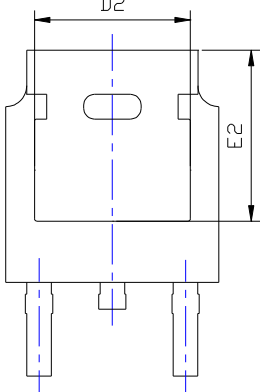
■ TO-252-B Package information



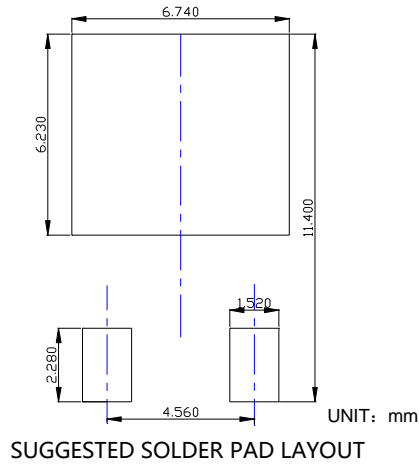
TOP VIEW



SIDE VIEW



BOTTOM VIEW



SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A1	0.000	---	0.008	0.000	---	0.200
A2	0.087	0.091	0.094	2.200	2.300	2.400
A3	0.035	0.039	0.043	0.900	1.000	1.100
b	0.026	0.030	0.034	0.660	0.760	0.860
c	0.018	0.020	0.023	0.460	0.520	0.580
D	0.256	0.260	0.264	6.500	6.600	6.700
D1	0.203	0.209	0.215	5.150	5.300	5.450
D2	0.181	0.189	0.195	4.600	4.800	4.950
E	0.390	0.398	0.406	9.900	10.100	10.300
E1	0.236	0.240	0.244	6.000	6.100	6.200
E2	0.203	0.209	0.215	5.150	5.300	5.450
e	0.090BSC			2.286BSC		
L	0.049	0.059	0.069	1.250	1.500	1.750
L1	0.035	---	0.050	0.900	---	1.270
L2	0.055	---	0.075	1.400	---	1.900
L3	0.240	0.310	0.039	0.600	0.800	1.000
L4	0.114REF			2.900REF		
θ	0°	---	10°	0°	---	10°

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.



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